

4K x 8/9 Dual-Port Static RAM with Sem, Int, Busy

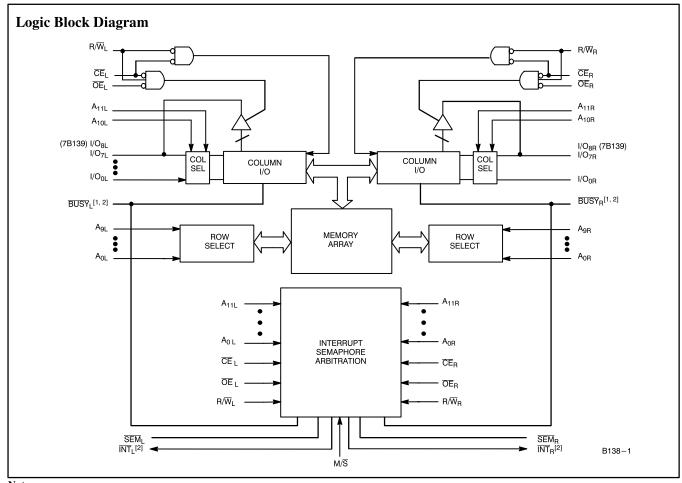
Features

- 0.8-micron BiCMOS for high performance
- High-speed access
 - -15 ns (com'l)
 - 25 ns (mil)
- Automatic power-down
- **Fully asynchronous operation**
- Master /Slave select pin allows bus width expansion to 16/18 bits or more
- Busy arbitration scheme provided
- Semaphores included to permit software handshaking between ports
- **INT** flag for port-to-port communication
- Available in 68-pin LCC/PLCC/PGA
- TTL compatible

Functional Description

The CY7B138 and CY7B139 are highspeed BiCMOS 4K x 8 and 4K x 9 dualport static RAMs. Various arbitration schemes are included on the CY7B138/9 to handle situations when multiple processors access the same piece of data. Two ports are provided permitting independent, asynchronous access for reads and writes to any location in memory. The CY7B138/9 can be utilized as a standalone 32-Kbit dual-port static RAM or multiple devices can be combined in order to function as a 16/18-bit or wider master/ slave dual-port static RAM. An M/\overline{S} pin is provided for implementing 16/18-bit or wider memory applications without the need for separate master and slave devices or additional discrete logic. Application areas include interprocessor/multiprocessor designs, communications status buffering, and dual-port video/graphics memory. Each port has independent control pins: chip enable (CE), read or write enable (R/\overline{W}) , and output enable (\overline{OE}) . Two flags are provided on each port (BUSY and INT). BUSY signals that the port is trying to access the same location currently being accessed by the other port. The interrupt flag (INT) permits communication between ports or systems by means of a mail box. The semaphores are used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphore logic is comprised of eight shared latches. Only one side can control the latch (semaphore) at any time. Control of a semaphore indicates that a shared resource is in use. An automatic power-down feature is controlled independently on each port by a chip enable (\overline{CE}) pin or \overline{SEM} pin.

The CY7B138 and CY7B139 are available in 68-pin LCCs, and PLCCs.



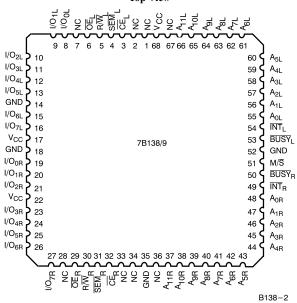
BUSY is an output in master mode and an input in slave mode.

2. Master: push-pull output and requires no pull-up resistor.



Pin Configurations





Pin Definitions

| Left Port | Right Port | Description |
|--|----------------------------|---|
| $I/O_{0L-7L(8L)}$ | $I/O_{0R-7R(8R)}$ | Data Bus Input/Output |
| A_{0L-11L} | A_{0R-11R} | Address Lines |
| $\overline{\text{CE}}_{	ext{L}}$ | CE _R | Chip Enable |
| OE _L | OE _R | Output Enable |
| R/\overline{W}_L | R/\overline{W}_R | Read/Write Enable |
| $\overline{\mathrm{SEM}}_{\mathrm{L}}$ | <u>SEM</u> _R | Semaphore Enable. When asserted LOW, allows access to eight semaphores. The three least significant bits of the address lines will determine which semaphore to write or read. The I/O_0 pin is used when writing to a semaphore. Semaphores are requested by writing a 0 into the respective location. |
| ĪNT _L | ĪNT _R | Interrupt Flag. \overline{INT}_L is set when right port writes location FFE and is cleared when left port reads location FFE. \overline{INT}_R is set when left port writes location FFF and is cleared when right port reads location FFF. |
| BUSY _L | BUSYR | Busy Flag |
| M/S | | Master or Slave Select |
| V _{CC} | | Power |
| GND | | Ground |

Selection Guide

| | | 7B138-15 7B139-15 | 7B138-25 7B139-25 | 7B138-35 7B139-35 | 7B138-55 7B139-55 |
|-----------------------------------|---------------------|----------------------|----------------------|----------------------|----------------------|
| Maximum Access Time (ns) | | 15 | 25 | 35 | 55 |
| Maximum Operating | Commercial | 260 | 220 | 210 | 210 |
| Current (mA) | Military/Industrial | | 280 | 250 | 250 |
| Maximum Standby | Commercial | 110 | 95 | 90 | 90 |
| Current for I _{SB1} (mA) | Military/Industrial | | 100 | 95 | 95 |



Maximum Ratings

not tested.)

Storage Temperature ... -65° C to $+150^{\circ}$ C

Ambient Temperature with

Power Applied ... -55° C to $+125^{\circ}$ C

Supply Voltage to Ground Potential ... -0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State ... -0.5V to +7.0V

DC Input Voltage^[3] ... -0.5V to +7.0V

(Above which the useful life may be impaired. For user guidelines,

| Static Discharge Voltage | >2001V |
|--------------------------------|---------|
| (per MIL-STD-883, Method 3015) | |
| Latch-Up Current | >200 mA |

Operating Range

| Range | Ambient Temperature | $ m v_{cc}$ |
|-------------------------|----------------------------------|-------------|
| Commercial | 0° C to $+70^{\circ}$ C | 5V ± 10% |
| Industrial | -40°C to +85°C | 5V ± 10% |
| Military ^[4] | −55°C to +125°C | 5V ± 10% |

Electrical Characteristics Over the Operating Range^[5]

| | | | | 7B13 7B13 | | 7B13 7B13 | | |
|--------------------|---|---|---------------|--------------|------|--------------|------|------|
| Parameter | Description | Test Conditions | | Min. | Max. | Min. | Max. | Unit |
| V_{OH} | Output HIGH Voltage | $V_{CC} = Min., I_{OH} = -4.0 \text{ m}.$ | A | 2.4 | | 2.4 | | V |
| V_{OL} | Output LOW Voltage | $V_{CC} = Min., I_{OL} = 4.0 \text{ mA}$ | | | 0.4 | | 0.4 | V |
| V_{IH} | Input HIGH Voltage | | | 2.2 | | 2.2 | | V |
| V_{IL} | Input LOW Voltage | | | | 0.8 | | 0.8 | V |
| I_{IX} | Input Leakage Current | $GND \le V_I \le V_{CC}$ | | -10 | +10 | -10 | +10 | μΑ |
| I_{OZ} | Output Leakage Current | Output Disabled, GND \leq V _O | $\leq V_{CC}$ | -10 | +10 | -10 | +10 | μΑ |
| I_{CC} | Operating Current | $V_{CC} = Max.,$ | Com'l | | 260 | | 220 | mA |
| | | $I_{OUT} = 0 \text{ mA},$ Outputs Disabled | Mil/Ind | | | | 280 | 1 1 |
| I_{SB1} | Standby Current | $\overline{\text{CE}}_{\text{L}} \text{ and } \overline{\text{CE}}_{\text{R}} \ge \text{V}_{\text{IH}},$ $f = f_{\text{MAX}}^{[6]}$ | Com'l | | 110 | | 95 | mA |
| | (Both Ports TTL Levels) | $f = f_{MAX}^{[0]}$ | Mil/Ind | | | | 100 | 1 |
| I _{SB2} | Standby Current | $\overline{\text{CE}}_{\text{L}}$ and $\overline{\text{CE}}_{\text{R}} \ge \text{V}_{\text{IH}}$, $f = f_{\text{MAX}}^{[6]}$ | Com'l | | 165 | | 145 | mA |
| | (One Port TTL Level) | $f = f_{MAX}^{[\mathfrak{o}]}$ | Mil/Ind | | | | 180 | 1 |
| I_{SB3} | Standby Current (Both Ports CMOS Levels) | Both Ports $\overline{\text{CE}}$ and $\overline{\text{CE}}_{R} \ge V_{CC} - 0.2V$, | Com'l | | 15 | | 15 | mA |
| | , , | $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{[6]}$ | Mil/Ind | | | | 30 | |
| I_{SB4} | Standby Current (One Port CMOS Level) | One Port \overline{CE}_L or $\overline{CE}_R \ge V_{CC} - 0.2V$, | Com'l | | 160 | | 140 | mA |
| | | $V_{\rm IN} \ge V_{\rm CC} - 0.2 \text{V or}$ $V_{\rm IN} \le 0.2 \text{V}$, Active Port Outputs, $f = f_{\rm MAX}^{[6]}$ | Mil/Ind | | | | 160 | |

- 3. Pulse width < 20 ns.
- 4. T_A is the "instant on" case temperature.
- 5. See the last page of this specification for Group A subgroup testing information.
- 6. $f_{MAX} = 1/t_{RC}$ = All inputs cycling at $f = 1/t_{RC}$ (except output enable). f = 0 means no address or control lines change. This applies only to inputs at CMOS level standby I_{SB3} .



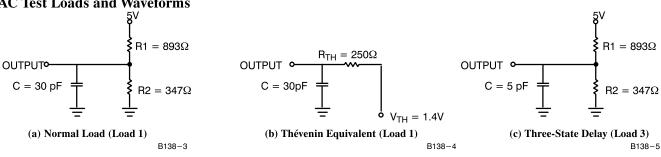
Electrical Characteristics Over the Operating Range^[5] (continued)

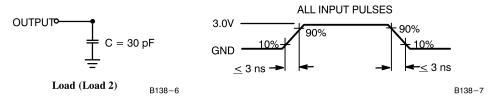
| | | | | | 8-35 9-35 | | 8-55 9-55 | |
|--------------------|---|--|---------------|------|--------------|------|--------------|------|
| Parameter | Description | Test Conditions | | Min. | Max. | Min. | Max. | Unit |
| V_{OH} | Output HIGH Voltage | $V_{CC} = Min., I_{OH} = -4.0 \text{ m}.$ | A | 2.4 | | 2.4 | | V |
| V_{OL} | Output LOW Voltage | $V_{CC} = Min., I_{OL} = 4.0 \text{ mA}$ | | | 0.4 | | 0.4 | V |
| V_{IH} | Input HIGH Voltage | | | 2.2 | | 2.2 | | V |
| V_{IL} | Input LOW Voltage | | | | 0.8 | | 0.8 | V |
| I_{IX} | Input Leakage Current | $GND \le V_I \le V_{CC}$ | | -10 | +10 | -10 | +10 | μΑ |
| I_{OZ} | Output Leakage Current | Output Disabled, GND \leq V _O | $\leq V_{CC}$ | -10 | +10 | -10 | +10 | μΑ |
| I_{CC} | Operating Current | $V_{CC} = Max.,$ $I_{OUT} = 0 \text{ mA},$ | Com'l | | 210 | | 210 | mA |
| | | Outputs Disabled | Mil/Ind | | 250 | | 250 | |
| I _{SB1} | Standby Current | $\overline{\text{CE}}_{\text{L}} \text{ and } \overline{\text{CE}}_{\text{R}} \geq \text{V}_{\text{IH}},$ $f = f_{\text{MAX}}^{[6]}$ | Com'l | | 90 | | 90 | mA |
| | (Both Ports TTL Levels) | $f = f_{MAX}^{[0]}$ | Mil/Ind | | 95 | | 95 | 1 |
| I_{SB2} | Standby Current | $\overline{\text{CE}}_{L}$ and $\overline{\text{CE}}_{R} \ge \text{V}_{IH}$, $f = f_{\text{MAX}}^{[6]}$ | Com'l | | 135 | | 135 | mA |
| | (One Port TTL Level) | $f = f_{MAX}^{[0]}$ | Mil/Ind | | 160 | | 160 | 1 |
| I_{SB3} | Standby Current (Both Ports CMOS Levels) | Both Ports $\overline{\text{CE}}$ and $\overline{\text{CE}}_{R} \ge V_{\text{CC}} - 0.2V$, | Com'l | | 15 | | 15 | mA |
| | , , , , , , , , , , , , , , , , , , , | $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{[6]}$ | Mil/Ind | | 30 | | 30 | |
| I_{SB4} | Standby Current (One Port CMOS Level) | One Port \overline{CE}_L or $\overline{CE}_R \ge V_{CC} - 0.2V$, | Com'l | | 130 | | 130 | mA |
| | | $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, Active Port Outputs, $f = f_{MAX}^{[6]}$ | Mil/Ind | | 140 | | 140 | |

Capacitance^[7]

| Parameter Description | | Test Conditions | Max. | Unit |
|-----------------------|--------------------|---|------|------|
| C_{IN} | Input Capacitance | $T_A = 25^{\circ}C, f = 1 \text{ MHz},$ | 10 | pF |
| C_{OUT} | Output Capacitance | $V_{CC} = 5.0V$ | 15 | рF |

AC Test Loads and Waveforms





Note:
7. Tested initially and after any design or process changes that may affect



Switching Characteristics Over the Operating Range^[5, 8]

| | | | 38-15 39-15 | 7B1. 7B1. | 38-25 39-25 | | 38-35 39-35 | | 38-55 39-55 | |
|-----------------------------------|-------------------------------------|------|----------------|--------------|----------------|------|----------------|------|----------------|------|
| Parameter | Description | Min. | Max. | Min. | Max. | Min. | Max. | Min. | Max. | Unit |
| READ CYCLE | | | | | | | | | | |
| t_{RC} | Read Cycle Time | 15 | | 25 | | 35 | | 55 | | ns |
| t_{AA} | Address to Data Valid | | 15 | | 25 | | 35 | | 55 | ns |
| t _{OHA} | Output Hold From Address Change | 3 | | 3 | | 3 | | 3 | | ns |
| t _{ACE} | CE LOW to Data Valid | | 15 | | 25 | | 35 | | 55 | ns |
| t_{DOE} | OE LOW to Data Valid | | 10 | | 15 | | 20 | | 25 | ns |
| t _{LZOE} [9. 10] | OE Low to Low Z | 3 | | 3 | | 3 | | 3 | | ns |
| t _{HZOE} [9, 10] | OE HIGH to High Z | | 10 | | 15 | | 20 | | 25 | ns |
| $t_{LZCE}^{[9, 10]}$ | CE LOW to Low Z | 3 | | 3 | | 3 | | 3 | | ns |
| t _{HZCE} [9, 10] | CE HIGH to High Z | | 10 | | 15 | | 20 | | 25 | ns |
| t_{PU} | CE LOW to Power-Up | 0 | | 0 | | 0 | | 0 | | ns |
| t_{PD} | CE HIGH to Power-Down | | 15 | | 25 | | 35 | | 55 | ns |
| WRITE CYC | | | | | | | | | | |
| t _{WC} | Write Cycle Time | 15 | | 25 | | 35 | | 55 | | ns |
| t _{SCE} | CE LOW to Write End | 12 | | 20 | | 30 | | 40 | | ns |
| t_{AW} | Address Set-Up to Write End | 12 | | 20 | | 30 | | 40 | | ns |
| t _{HA} | Address Hold From Write End | 2 | | 2 | | 2 | | 2 | | ns |
| t_{SA} | Address Set-Up to Write Start | 0 | | 0 | | 0 | | 0 | | ns |
| t_{PWE} | Write Pulse Width | 12 | | 20 | | 25 | | 30 | | ns |
| t_{SD} | Data Set-Up to Write End | 10 | | 15 | | 15 | | 20 | | ns |
| $t_{ m HD}$ | Data Hold From Write End | 0 | | 0 | | 0 | | 0 | | ns |
| t _{HZWE} ^[10] | R/\overline{W} LOW to High Z | | 10 | | 15 | | 20 | | 25 | ns |
| $t_{LZWE}^{[10]}$ | R/W HIGH to Low Z | 3 | | 3 | | 3 | | 3 | | ns |
| t _{WDD} [11] | Write Pulse to Data Delay | | 30 | | 50 | | 60 | | 70 | ns |
| t _{DDD} [11] | Write Data Valid to Read Data Valid | | 25 | | 30 | | 35 | | 40 | ns |
| BUSY TIMIN | $\mathbf{NG}^{[12]}$ | | | | | | | | | |
| $t_{ m BLA}$ | BUSY LOW from Address Match | | 15 | | 20 | | 20 | | 45 | ns |
| t _{BHA} | BUSY HIGH from Address Mismatch | | 15 | | 20 | | 20 | | 40 | ns |
| $t_{ m BLC}$ | BUSY LOW from CE LOW | | 15 | | 20 | | 20 | | 40 | ns |
| t _{BHC} | BUSY HIGH from CE HIGH | | 15 | | 20 | | 20 | | 35 | ns |
| t_{PS} | Port Set-Up for Priority | 5 | | 5 | | 5 | | 5 | | ns |
| $t_{ m WB}$ | R/W LOW after BUSY LOW | 0 | | 0 | | 0 | | 0 | | ns |
| $t_{ m WH}$ | R/W HIGH after BUSY HIGH | 13 | | 20 | | 30 | | 40 | | ns |
| $t_{\mathrm{BDD}}^{[13]}$ | BUSY HIGH to Data Valid | | Note 13 | | Note 13 | | Note 13 | | Note 13 | ns |
| INTERRUPT | TIMING ^[12] | | | | | | | | | |
| t_{INS} | INT Set Time | | 15 | | 25 | | 25 | | 30 | ns |
| t _{INR} | INT Reset Time | | 15 | | 25 | | 25 | | 30 | ns |
| SEMAPHOR | RE TIMING | | | | | | | | | |
| t _{SOP} | SEM Flag Update Pulse (OE or SEM) | 10 | | 10 | | 15 | | 20 | | ns |
| t _{SWRD} | SEM Flag Write to Read Time | 5 | | 5 | | 5 | | 5 | | ns |
| t _{SPS} | SEM Flag Contention Window | 5 | | 5 | | 5 | | 5 | | ns |

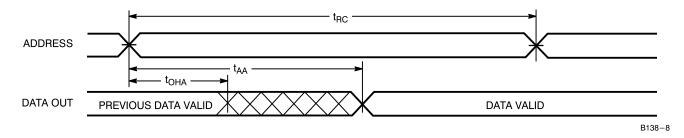
- 8. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OI}/I_{OH} and 30-pF load capacitance.
- 9. At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZOE} is less than t_{LZCE}.
- 10. Test conditions used are Load 3.

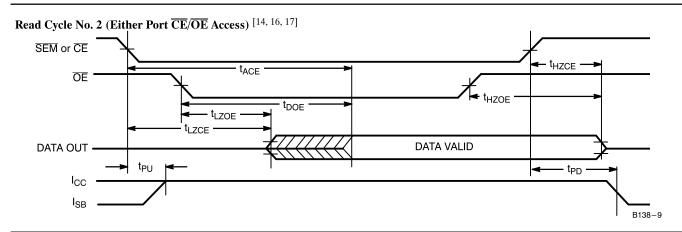
- 11. For information on part-to-part delay through RAM cells from writing port to reading port, refer to Read Timing with Port-to-Port Delay waveform.
- 12. Test conditions used are Load 2.
- 13 t_{BDD} is a calculated parameter and is the greater of t_{WDD} t_{PWE} (actual) or t_{DDD} t_{SD} (actual).



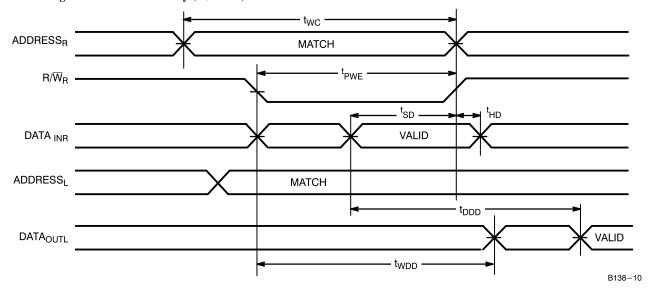
Switching Waveforms

Read Cycle No. 1 (Either Port Address Access)^[14, 15]





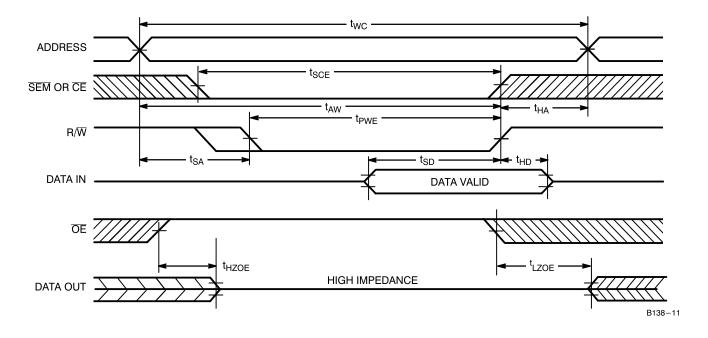
Read Timing with Port-to-Port Delay (M/ \overline{S} = L)^[18, 19]



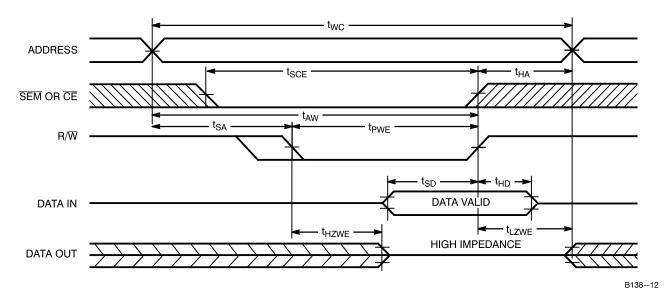
- 14. R/\overline{W} is HIGH for read cycle.
- 15. Device is continuously selected $\overline{CE}=LOW$ and $\overline{OE}=LOW$. This waveform cannot be used for semaphore reads.
- 16. Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.
- 17. $\overline{CE}_L = L$, $\overline{SEM} = H$ when accessing RAM. $\overline{CE} = H$, $\overline{SEM} = L$ when accessing semaphores.
- 18. $\overline{\text{BUSY}} = \text{HIGH}$ for the writing port.
- 19. $\overline{\text{CE}}_{\text{L}} = \overline{\text{CE}}_{\text{R}} = \text{LOW}.$



Write Cycle No. 1: \overline{OE} Three-States Data I/Os (Either Port)[20, 21, 22]



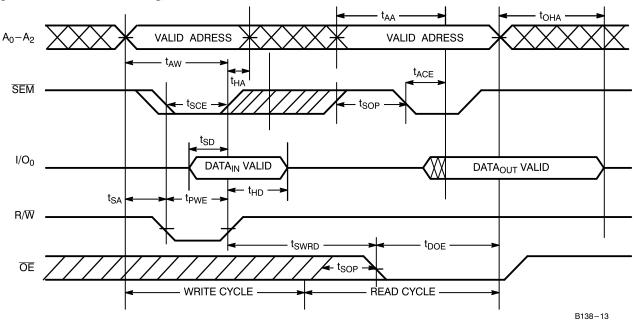
Write Cycle No. 2: R/\overline{W} Three-States Data I/Os (Either Port)[20, 22, 23]



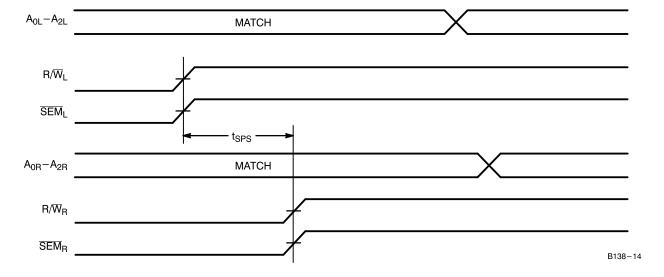
- 20. The internal write time of the memory is defined by the overlap of \(\overline{CE}\) or \(\overline{SEM}\) LOW and R/\(\overline{W}\) LOW. Both signals must be LOW to initiate a write, and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
- 21. If \overline{OE} is LOW during a R/ \overline{W} controlled write cycle, the write pulse width must be the larger of t_{PWE} or $(t_{HZWE} + t_{SD})$ to allow the I/O
- drivers to turn off and data to be placed on the bus for the required t_{SD} . If \overline{OE} is HIGH during a R/W controlled write cycle (as in this example), this requirement does not apply and the write pulse can be as short as the specified t_{PWE} .
- 22. R/\overline{W} must be HIGH during all address transitions.
- 23. Data I/O pins enter high impedance when \overline{OE} is held LOW during write.



Semaphore Read After Write Timing, Either Side^[24]



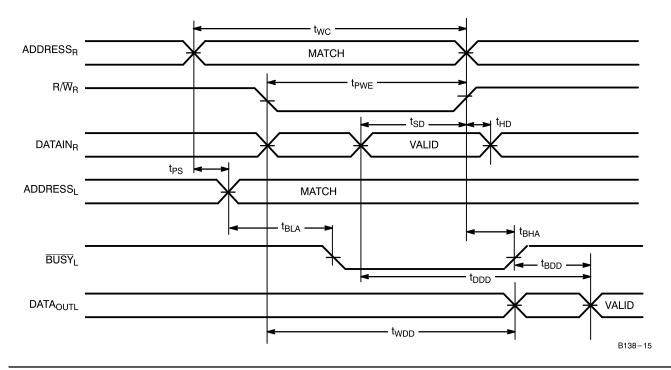
Timing Diagram of Semaphore Contention^[25, 26, 27]



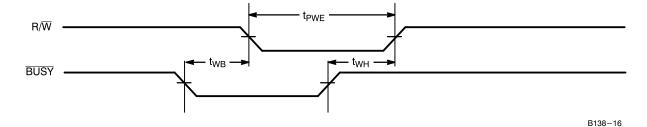
- Notes: 24. \overrightarrow{CE} = HIGH for the duration of the above timing (both write and read
- 25. $I/O_{0R} = I/O_{0L} = LOW$ (request semaphore); $\overline{CE}_R = \overline{CE}_L = HIGH$
- 26. Semaphores are reset (available to both ports) at cycle start.
- 27. If t_{SPS} is violated, the semaphore will definitely be obtained by one side or the other, but there is no guarantee which side will control the semaphore.



Timing Diagram of Read with \overline{BUSY} $(M/\overline{S}=HIGH)^{[19]}$



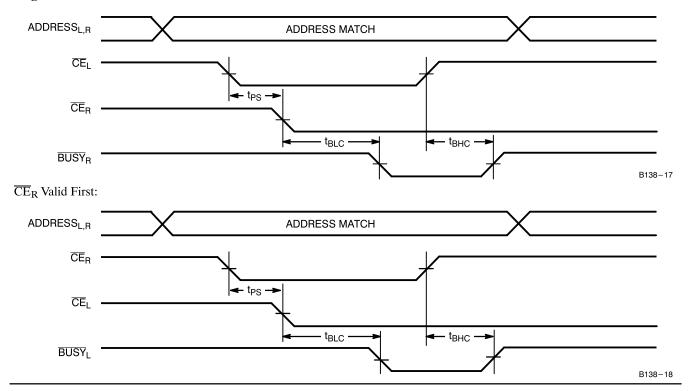
Write Timing with Busy Input $(M/\overline{S} = LOW)$





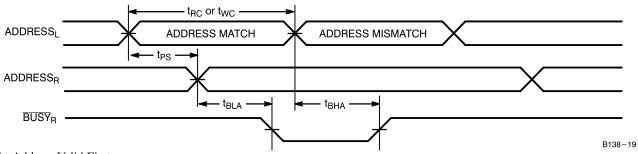
Busy Timing Diagram No. 1 (CE Arbitration)^[28]

 $\overline{\text{CE}}_{L}$ Valid First:

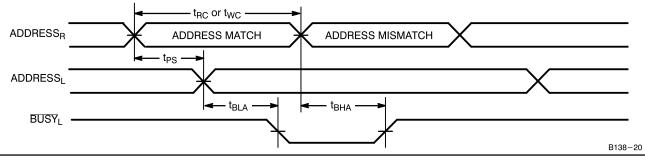


Busy Timing Diagram No. 2 (Address Arbitration)^[28]

Left Address Valid First:



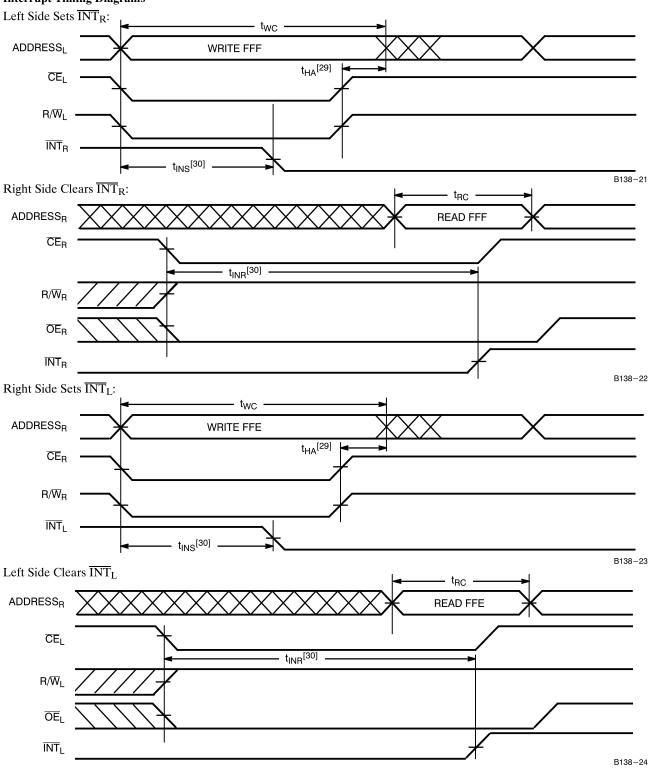
Right Address Valid First:



^{28.} If t_{PS} is violated, the busy signal will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.



Interrupt Timing Diagrams



Notes:

29. t_{HA} depends on which enable pin (\overline{CE}_L or R/\overline{W}_L) is deasserted first.

30. t_{INS} or t_{INR} depends on which enable pin $(\overline{CE}_L$ or $R/\overline{W}_L)$ is asserted last.



Architecture

The CY7B138/9 consists of an array of 4K words of 8/9 bits each of dual-port RAM cells, I/O and address lines, and control signals $(\overline{CE}, \overline{OE}, R/\overline{W})$. These control pins permit independent access for reads or writes to any location in memory. To handle simultaneous writes/reads to the same location, a \overline{BUSY} pin is provided on each port. Two interrupt (\overline{INT}) pins can be utilized for port-to-port communication. Two semaphore (\overline{SEM}) control pins are used for allocating shared resources. With the M/ \overline{S} pin, the CY7B138/9 can function as a master (\overline{BUSY}) pins are outputs) or as a slave (\overline{BUSY}) pins are inputs). The CY7B138/9 has an automatic power-down feature controlled by \overline{CE} . Each port is provided with its own output enable control (\overline{OE}) , which allows data to be read from the device.

Functional Description

Write Operation

Data must be set up for a duration of t_{SD} before the rising edge of R/\overline{W} in order to guarantee a valid write. A write operation is controlled by either the \overline{OE} pin (see Write Cycle No. 1 waveform) or the R/\overline{W} pin (see Write Cycle No. 2 waveform). Data can be written to the device t_{HZOE} after the \overline{OE} is deasserted or t_{HZWE} after the falling edge of R/\overline{W} . Required inputs for non-contention operations are summarized in *Table 1*.

If a location is being written to by one port and the opposite port attempts to read that location, a port-to-port flowthrough delay must be met before the data is read on the output; otherwise the data read is not deterministic. Data will be valid on the port $t_{\mbox{\scriptsize DDD}}$ after the data is presented on the other port.

Read Operation

When reading the device, the user must assert both the \overline{OE} and \overline{CE} pins. Data will be available t_{ACE} after \overline{CE} or t_{DOE} after \overline{OE} is asserted. If the user of the CY7B138/9 wishes to access a semaphore flag, then the \overline{SEM} pin must be asserted instead of the \overline{CE} pin.

Interrupts

The interrupt flag (\overline{INT}) permits communications between ports. When the left port writes to location FFF, the right port's interrupt flag (\overline{INT}_R) is set. This flag is cleared when the right port reads that same location. Setting the left port's interrupt flag (\overline{INT}_L) is accomplished when the right port writes to location FFE. This flag is cleared when the left port reads location FFE. The message at FFF or FFE is user-defined. See *Table 2* for input requirements for $\overline{INT}.\overline{INT}_R$ and \overline{INT}_L are push-pull outputs and do not require pullup resistors to operate. \overline{BUSY}_L and \overline{BUSY}_R in master mode are push-pull outputs and do not require pull-up resistors to operate.

Busy

The CY7B138/9 provides on-chip arbitration to alleviate simultaneous memory location access (contention). If both ports' \overline{CE} s are asserted and an address match occurs within t_{PS} of each other the Busy logic will determine which port has access. If t_{PS} is violated, one port will definitely gain permission to the location, but it is not guaranteed which one. \overline{BUSY} will be asserted t_{BLA} after an address match or t_{BLC} after \overline{CE} is taken LOW.

Master/Slave

A M/\overline{S} pin is provided in order to expand the word width by configuring the device as either a master or a slave. The \overline{BUSY} output of the master is connected to the \overline{BUSY} input of the slave. This will allow the device to interface to a master device with no external components. Writing of slave devices must be delayed until after the \overline{BUSY} input has settled. Otherwise, the slave chip may begin a write cycle during a contention situation. When presented as a HIGH input, the M/\overline{S} pin allows the device to be used as a master and therefore the \overline{BUSY} line is an output. \overline{BUSY} can then be used to send the arbitration outcome to a slave.

Semaphore Operation

The CY7B138/9 provides eight semaphore latches, which are separate from the dual-port memory locations. Semaphores are used to reserve resources that are shared between the two ports. The state of the semaphore indicates that a resource is in use. For example, if the left port wants to request a given resource, it sets a latch by writing a zero to a semaphore location. The left port then verifies its success in setting the latch by reading it. After writing to the semaphore, \overline{SEM} or \overline{OE} must be deasserted for t_{SOP} before attempting to read the semaphore. The semaphore value will be available t_{SWRD} + t_{DOE} after the rising edge of the semaphore write. If the left port was successful (reads a zero), it assumes control over the shared resource, otherwise (reads a one) it assumes the right port has control and continues to poll the semaphore. When the right side has relinquished control of the semaphore (by writing a one), the left side will succeed in gaining control of the a semaphore. If the left side no longer requires the semaphore, a one is written to cancel its request.

Semaphores are accessed by asserting \overline{SEM} LOW. The \overline{SEM} pin functions as a chip enable for the semaphore latches (\overline{CE} must remain HIGH during \overline{SEM} LOW). A_{0-2} represents the semaphore address. \overline{OE} and R/\overline{W} are used in the same manner as a normal memory access. When writing or reading a semaphore, the other address pins have no effect.

When writing to the semaphore, only I/O₀ is used. If a zero is written to the left port of an unused semaphore, a one will appear at the same semaphore address on the right port. That semaphore can now only be modified by the side showing zero (the left port in this case). If the left port now relinquishes control by writing a one to the semaphore, the semaphore will be set to one for both sides. However, if the right port had requested the semaphore (written a zero) while the left port had control, the right port would immediately own the semaphore as soon as the left port released it. *Table 3* shows sample semaphore operations.

When reading a semaphore, all eight data lines output the semaphore value. The read value is latched in an output register to prevent the semaphore from changing state during a write from the other port. If both ports attempt to access the semaphore within t_{SPS} of each other, the semaphore will definitely be obtained by one side or the other, but there is no guarantee which side will control the semaphore.

Initialization of the semaphore is not automatic and must be reset during initialization program at power-up. All semaphores on both sides should have a one written into themn at initialization from both sides to assure that they will be free when needed.



Table 1. Non-Contending Read/Write

| | Inp | outs | | Outputs | |
|----|-----|------|-----|--------------------|---------------------------|
| CE | R/W | ŌE | SEM | I/O ₀₋₇ | Operation |
| Н | X | X | Н | High Z | Power-Down |
| Н | Н | L | L | Data Out | Read Data in Semaphore |
| X | X | Н | X | High Z | I/O Lines Disabled |
| Н | 7 | X | L | Data In | Write to Semaphore |
| L | Н | L | Н | Data Out | Read |
| L | L | X | Н | Data In | Write |
| L | X | X | L | | Illegal Condition |

Table 2. Interrupt Operation Example (assumes $\overline{BUSY}_L {=} \overline{BUSY}_R {=} HIGH)$

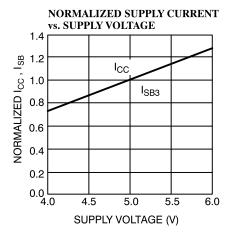
| | Left Port | | | | Right Port | | | | | |
|-----------------|-----------|--|---|-----|------------|----|----|------------|-----|---|
| Function | R/W | R/\overline{W} \overline{CE} \overline{OE} A_{0-11} \overline{INT} | | | R/W | CE | ŌE | A_{0-11} | INT | |
| Set Left INT | X | X | X | X | L | L | L | X | FFE | X |
| Reset Left INT | X | L | L | FFE | Н | X | X | X | X | X |
| Set Right INT | L | L | X | FFF | X | X | X | X | X | L |
| Reset Right INT | X | X | X | X | X | X | L | L | FFF | Н |

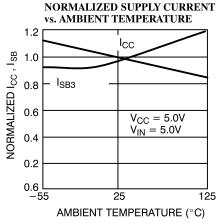
Table 3. Semaphore Operation Example

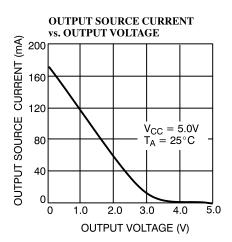
| Function | I/O 0 Left | I/O 0 Right | Status |
|----------------------------------|------------|-------------|---|
| No action | 1 | 1 | Semaphore free |
| Left port writes semaphore | 0 | 1 | Left port obtains semaphore |
| Right port writes 0 to semaphore | 0 | 1 | Right side is denied access |
| Left port writes 1 to semaphore | 1 | 0 | Right port is granted access to semaphore |
| Left port writes 0 to semaphore | 1 | 0 | No change. Left port is denied access |
| Right port writes 1 to semaphore | 0 | 1 | Left port obtains semaphore |
| Left port writes 1 to semaphore | 1 | 1 | No port accessing semaphore address |
| Right port writes 0 to semaphore | 1 | 0 | Right port obtains semaphore |
| Right port writes 1 to semaphore | 1 | 1 | No port accessing semaphore |
| Left port writes 0 to semaphore | 0 | 1 | Left port obtains semaphore |
| Left port writes 1 to semaphore | 1 | 1 | No port accessing semaphore |

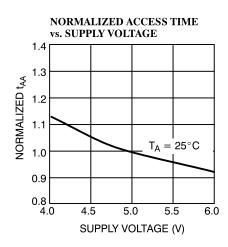


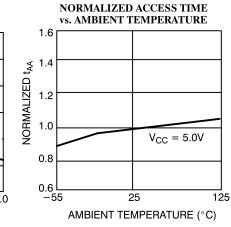
Typical DC and AC Characteristics

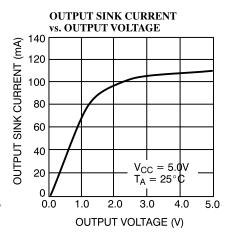


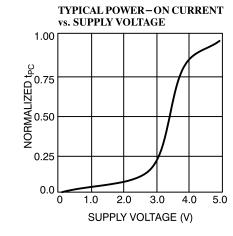


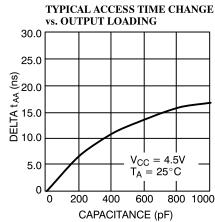


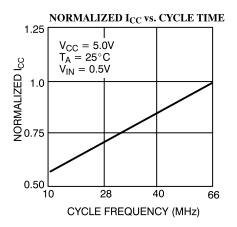














Ordering Information

| Speed (ns) | Ordering Code | Package Name | Package Type | Operating Range |
|------------|---------------|-----------------|-------------------------------------|--------------------|
| 15 | CY7B138-15JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| 25 | CY7B138-25JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B138-25JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |
| | CY7B138-25LMB | L81 | 68-Square Leadless Chip Carrier | Military |
| 35 | CY7B138-35JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B138-35JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |
| | CY7B138-35LMB | L81 | 68-Square Leadless Chip Carrier | Military |
| 55 | CY7B138-55JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B138-55JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |

| Speed (ns) | Ordering Code | Package Type | Package Type | Operating Range |
|------------|---------------|-----------------|-------------------------------------|--------------------|
| 15 | CY7B139-15JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| 25 | CY7B139-25JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B139-25JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |
| | CY7B139-25LMB | L81 | 68-Square Leadless Chip Carrier | Military |
| 35 | CY7B139-35JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B139-35JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |
| | CY7B139-35LMB | L81 | 68-Square Leadless Chip Carrier | Military |
| 55 | CY7B139-55JC | J81 | 68-Lead Plastic Leaded Chip Carrier | Commercial |
| | CY7B139-55JI | J81 | 68-Lead Plastic Leaded Chip Carrier | Industrial |



MILITARY SPECIFICATIONS Group A Subgroup Testing DC Characteristics

| Parameter | Subgroups |
|----------------------|-----------|
| V _{OH} | 1, 2, 3 |
| $V_{ m OL}$ | 1, 2, 3 |
| $V_{ m IH}$ | 1, 2, 3 |
| V _{IL} Max. | 1, 2, 3 |
| I_{IX} | 1, 2, 3 |
| I_{OZ} | 1, 2, 3 |
| I_{CC} | 1, 2, 3 |
| I_{SB1} | 1, 2, 3 |
| I_{SB2} | 1, 2, 3 |
| I_{SB3} | 1, 2, 3 |
| I_{SB4} | 1, 2, 3 |

Switching Characteristics

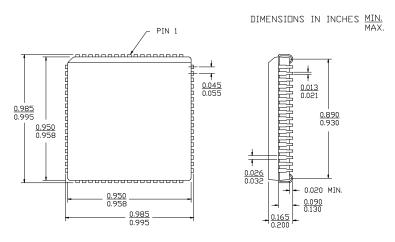
| Parameter | Subgroups | | | |
|-----------------------|-----------------|--|--|--|
| READ CYCLE | | | | |
| t _{RC} | 7, 8, 9, 10, 11 | | | |
| t_{AA} | 7, 8, 9, 10, 11 | | | |
| t _{OHA} | 7, 8, 9, 10, 11 | | | |
| t _{ACE} | 7, 8, 9, 10, 11 | | | |
| t _{DOE} | 7, 8, 9, 10, 11 | | | |
| WRITE CYCLE | | | | |
| $t_{ m WC}$ | 7, 8, 9, 10, 11 | | | |
| t _{SCE} | 7, 8, 9, 10, 11 | | | |
| t_{AW} | 7, 8, 9, 10, 11 | | | |
| t _{HA} | 7, 8, 9, 10, 11 | | | |
| t_{SA} | 7, 8, 9, 10, 11 | | | |
| t_{PWE} | 7, 8, 9, 10, 11 | | | |
| t_{SD} | 7, 8, 9, 10, 11 | | | |
| t _{HD} | 7, 8, 9, 10, 11 | | | |
| BUSY/INTERRUPT TIMING | | | | |
| t _{BLA} | 7, 8, 9, 10, 11 | | | |
| t _{BHA} | 7, 8, 9, 10, 11 | | | |
| t _{BLC} | 7, 8, 9, 10, 11 | | | |
| t _{BHC} | 7, 8, 9, 10, 11 | | | |
| t_{PS} | 7, 8, 9, 10, 11 | | | |
| $t_{ m INS}$ | 7, 8, 9, 10, 11 | | | |
| t _{INR} | 7, 8, 9, 10, 11 | | | |
| BUSY TIMING | | | | |
| $t_{ m WB}$ | 7, 8, 9, 10, 11 | | | |
| t _{WH} | 7, 8, 9, 10, 11 | | | |
| t _{BDD} | 7, 8, 9, 10, 11 | | | |
| t _{DDD} | 7, 8, 9, 10, 11 | | | |
| $t_{ m WDD}$ | 7, 8, 9, 10, 11 | | | |

Document #: 38-00162-G

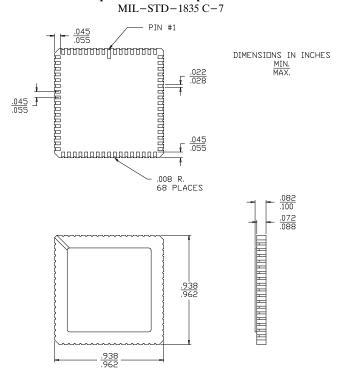


Package Diagrams

68-Lead Plastic Leaded Chip Carrier J81



68-Square Leadless Chip Carrier L81



[©] Cypress Semiconductor Corporation, 1994. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress Semiconductor Corporation product. Nor does it convey or imply any license under patent or other rights. Cypress Semiconductor does not authorize its products for use as critical components in life-support systems where a malfunction or failure of the product may reasonably be expected to result in significant injury to the user. The inclusion of Cypress Semiconductor products in life-support systems applications implies that the manufacturer assumes all risk of such use and in so doing indemnifies Cypress Semiconductor against all damages.